

Silicon NPN Power Transistors

2SC3063

DESCRIPTION

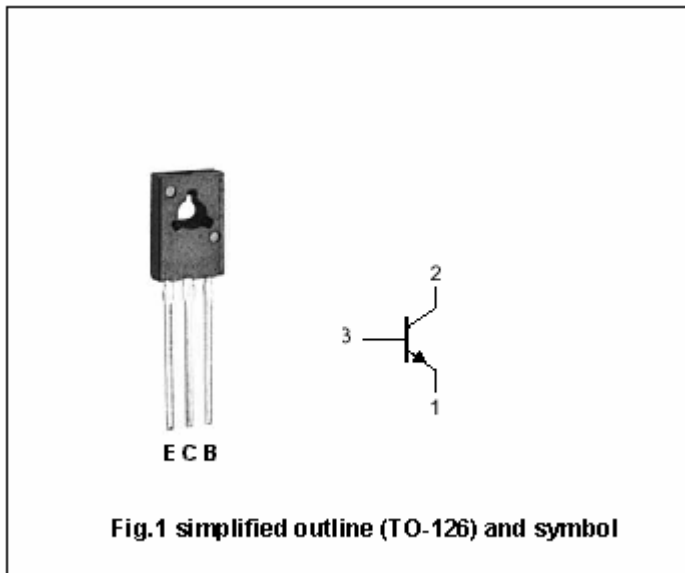
- With TO-126 package
- High V_{CEO}
- Low C_{OB}

APPLICATIONS

- For TV video output amplification

PINNING (see Fig.2)

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		0.1	A
I_{CM}	Collector current-peak		0.2	A
P_C	Collector power dissipation		1.2	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =30mA ; I _B =3mA			1.5	V
V _{BE}	Base-emitter on voltage	I _C =30mA ; V _{CE} =10V			1.2	V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =10 μ A ; I _E =0	300			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =100 μ A ; I _B =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10 μ A ; I _C =0	7			V
h _{FE}	DC current gain	I _C =5mA ; V _{CE} =50V	50		250	
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =30V ; f=1MHz		2.4		pF
f _T	Transition frequency	I _E =-20mA ; V _{CB} =30V	70			MHz

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PACKAGE OUTLINE

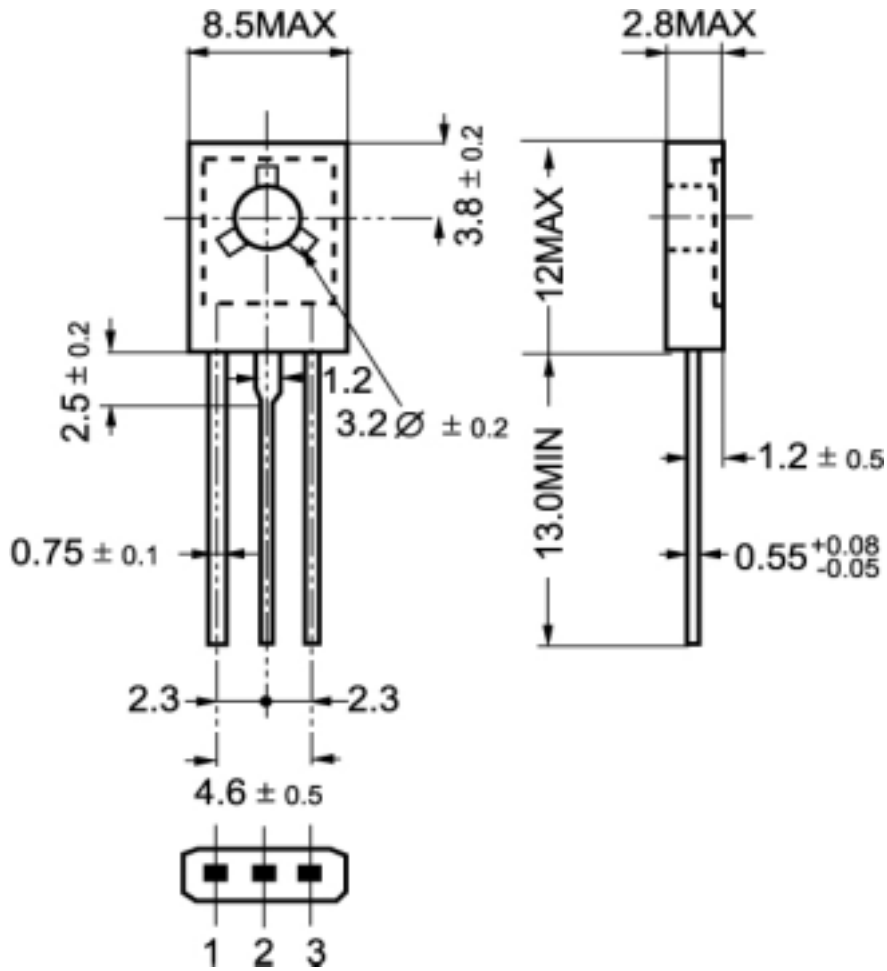


Fig.2 outline dimensions

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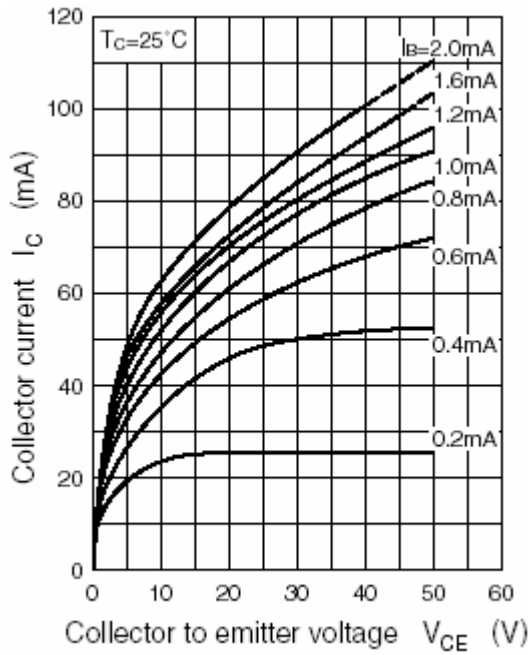


Fig.3 Static Characteristic

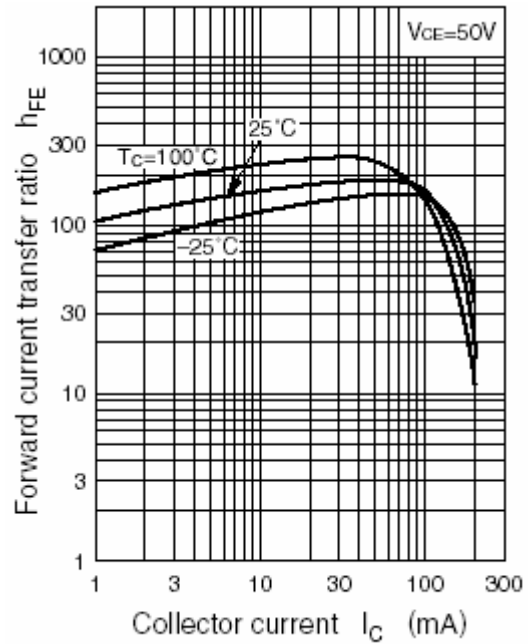


Fig.4 DC current Gain

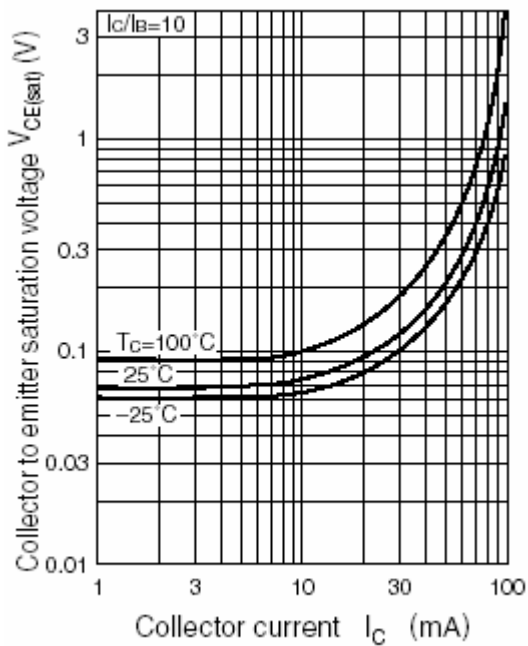


Fig.5 Collector-Emitter Saturation Voltage

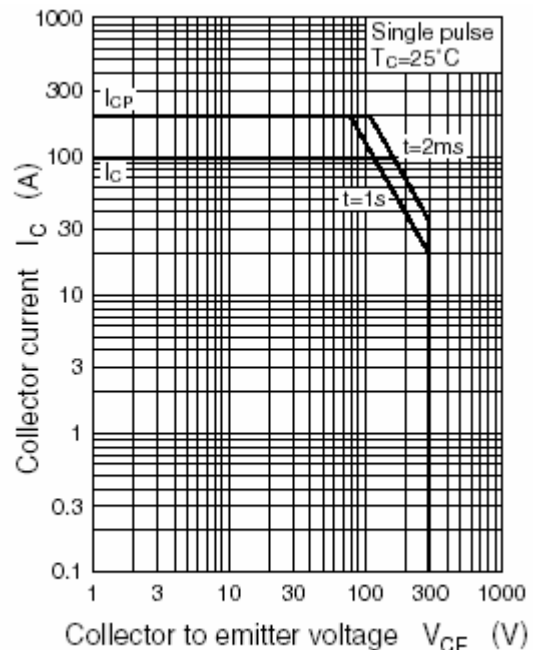


Fig.6 Safe Operating Area